

In the claims:

Please substitute the following full listing of claims for the claims as originally filed or most recently amended.

1. (Currently Amended) A field effect transistor comprising  
a transistor portion comprising a source, drain and gate formed on or in a semiconductor layer of a first conductivity type,  
a body contact to said semiconductor layer, and  
a body control contact of a conductivity type opposite said first conductivity type and interposed between said gate and said body contact to function as a pass transistor gate between said transistor portion and said body contact.
2. (Original) A field effect transistor as recited in claim 1, further including  
a connection between said gate and said body control contact.
3. (Currently Amended) A field effect transistor as recited in claim 2, wherein said body contact to said semiconductor layer is a region of said first conductivity type.
4. (Currently Amended) A field effect transistor as recited in claim 1, wherein body said contact to said semiconductor layer is a region of said first conductivity type.
5. (Currently Amended) A field effect transistor as recited in claim 1, wherein said body contact to said semiconductor layer is connected to a low voltage opposite in polarity to a voltage applied to said field effect transistor.

6. (Original) A field effect transistor as recited in claim 1, wherein said semiconductor layer is formed on an insulator on a substrate.

7. (Original) A field effect transistor as recited in claim 1,  
wherein said semiconductor layer is a silicon layer of a silicon-on-insulator substrate.

8. (Original) A field effect transistor as recited in claim 1, wherein a thickness of said semiconductor layer is approximately 800Å and said body control contact extends approximately 300Å to 350Å into said semiconductor layer.

9. (Currently Amended) An integrated circuit comprising

a plurality of transistor portions comprising a source, drain and gate formed on or in a semiconductor layer of a first conductivity type,

a body contact to said semiconductor layer, and

a body control contact of a conductivity type opposite said first conductivity type and interposed between said gate and said body contact to function as a pass transistor gate between at least one of said transistor portions and said body contact.

10. (Original) An integrated circuit as recited in claim 9, further including

a connection between said gate and said body control contact.

11. (Currently Amended) An integrated circuit as recited in claim 10, wherein said body contact to said semiconductor layer is a region of said first conductivity type.

12. (Currently Amended) An integrated circuit as recited in claim 9, wherein said body contact to said semiconductor layer is a region of said first conductivity type.

13. (Currently Amended) An integrated circuit as recited in claim 9, wherein said body contact to said semiconductor layer is connected to a low voltage opposite in polarity to a voltage applied to said field effect transistor.

14. (Original) An integrated circuit as recited in claim 9, wherein said semiconductor layer is formed on an insulator on a substrate.

15. (Original) An integrated circuit as recited in claim 9,  
wherein said semiconductor layer is a silicon layer of a silicon-on-insulator substrate.

16. (Currently Amended) An integrated circuit as recited in claim 9, wherein said plurality of transistor portions[[.]] include a complementary transistor pair.

17. (Currently Amended) ~~A field effect transistor~~ An integrated circuit as recited in claim ~~1~~ 9, wherein a thickness of said semiconductor layer is approximately 800Å and said body control contact extends approximately 300Å to 350Å into said semiconductor layer.

18. (Currently Amended) A portable electronic device comprising

a portable power supply, and

an integrated circuit, said integrated circuit comprising

a plurality of transistor portions comprising a source, drain and gate formed on or in a semiconductor layer of a first conductivity type,

a body contact to said semiconductor layer, and

a body control contact of a conductivity type opposite said first conductivity type and interposed between said gate and said body contact to function as a pass transistor gate between at least one of said transistor portions and said body contact.

19. (Original) A portable electronic device as recited in claim 18, wherein said integrated circuit further includes

a connection between a gate a said transistor portion and said body control contact.

20. (Original) A portable electronic device as recited in claim 18, wherein said plurality of transistor portions include a complementary transistor pair.